

The Challenge of Metrology in the 450 mm Wafer Transition Process

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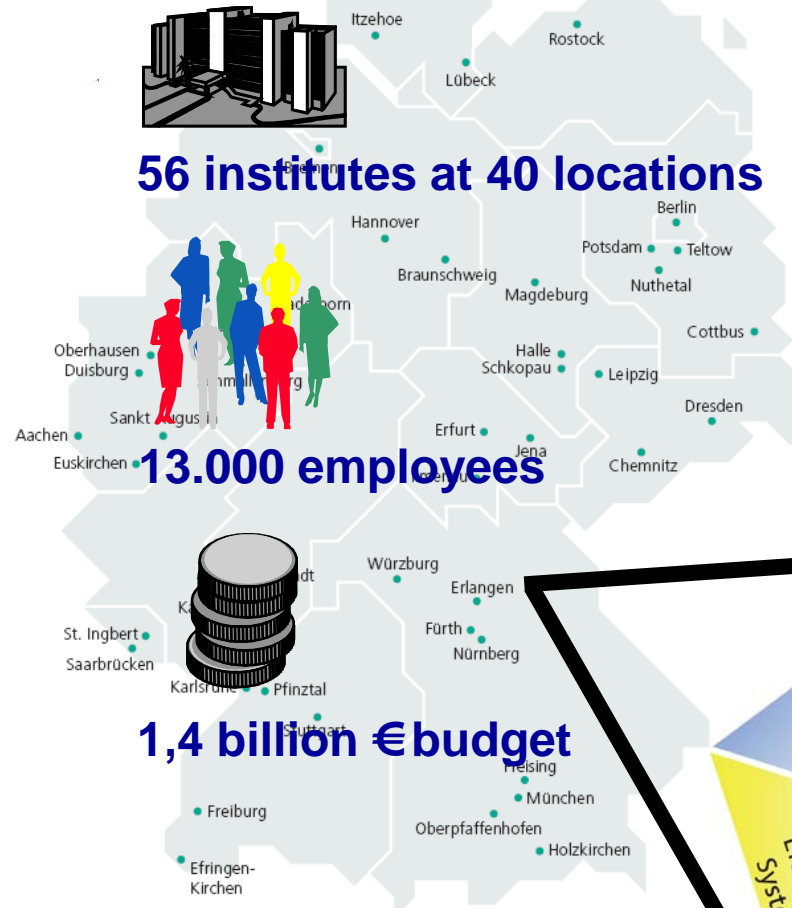


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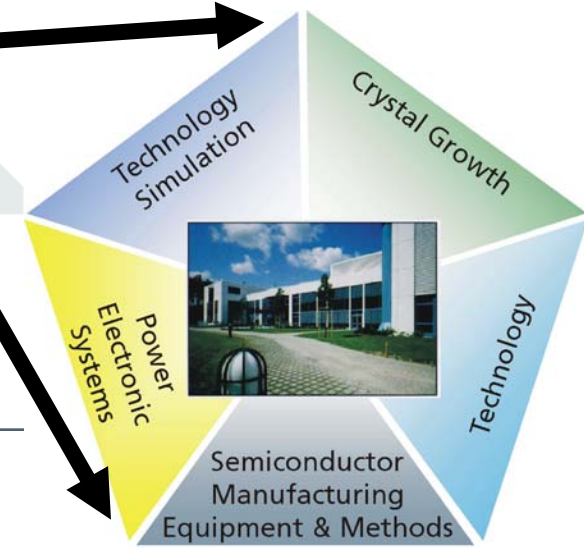
Founded in 1949 in Munich, Germany, the Fraunhofer-Gesellschaft with its numerous institutes is the **leading establishment of applied research in Germany**

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Fraunhofer Profile



- Microelectronics
- Production
- Information and Communication Technology
- Materials and Components
- Life Sciences
- Surface Technology and Photonics



-Introduction

- Definition of Metrology
- Metrology and Characterization

- Metrology in Semiconductor Manufacturing

- A bit of History – Introduction and Development of 300 mm
- Metrology in Production
- Production Ramp curve

- 450 mm Metrology Tools

- Impact of 450 mm Wafer Diameter on Equipment and Metrology
- Potential Development Topics for 450mm Metrology Tools
- Priorities in 450 mm

- Advanced Process Control

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- Network in Metrology
- 450 mm Metrology Platform
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Introduction

Metrology:

(Greek) *metron* (measure)

+ *logos* (study of)

Metrology includes all theoretical and practical aspects of measurement.

Metrology

- “The science of measurement, embracing both experimental and theoretical determinations at any level of uncertainty in any field of science and technology.”

Characterization

- “To describe the properties of a studied object by appropriate metrology”

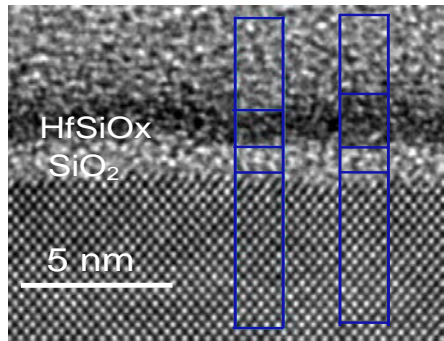
Inspection

- „An inspection is, most generally, an organized examination or formal evaluation exercise. It involves the measurements, tests, and gauges applied to certain characteristics in regard to an object or activity. The results are usually compared to specified requirements and standards for determining whether the item or activity is in line with these targets. Inspections are usually non-destructive.”

source www.wikipedia.org (2009)



Introduction



HfSiOx: 1.4 ± 0.5 nm 2.1 ± 0.5 nm
SiO₂: 1.1 ± 0.5 nm 1.1 ± 0.5 nm

Analysis at atomic scale performed with
XTEM @ CNR & **MEIS** @ Daresburg
Laboratory (USAL) (ANNA –project FP6 EC
contract 026134-R113)



Metrology and Characterization in Nanotechnologies

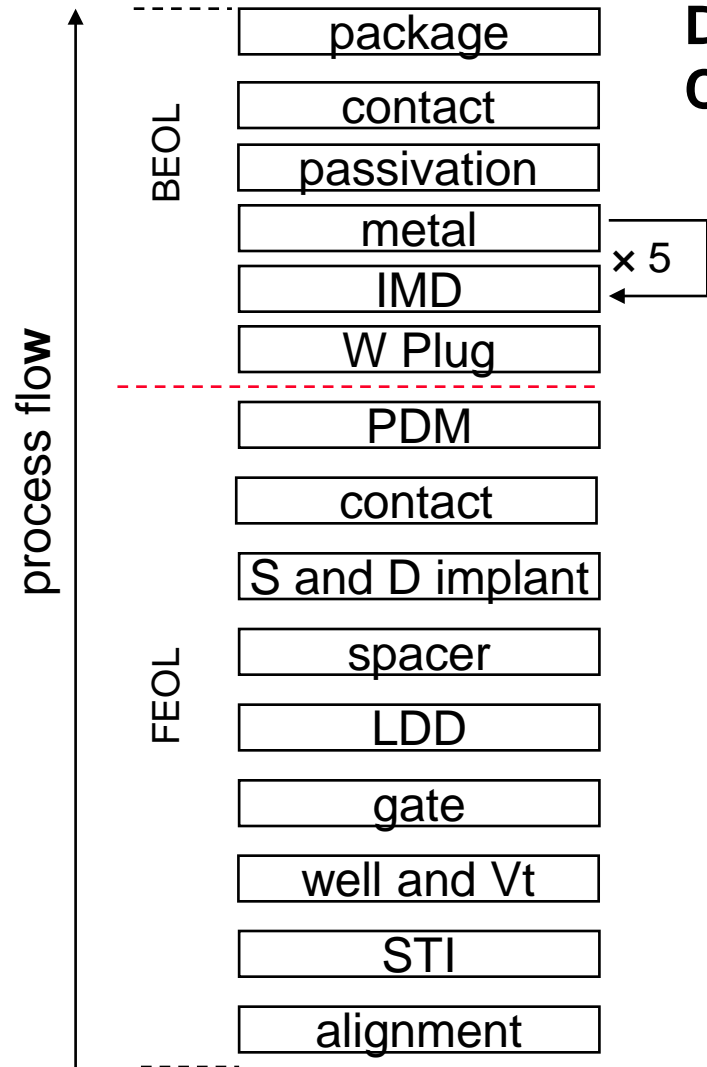
- understanding and controlling of dimensions, materials properties, and defects towards **atomic level** is required (e.g. 1.5 nm HfSiOx layer)
- **improving of capabilities** of metrology and analysis equipment (e.g. 3D at atomic scale) poses huge challenges

Semiconductor Manufacturing

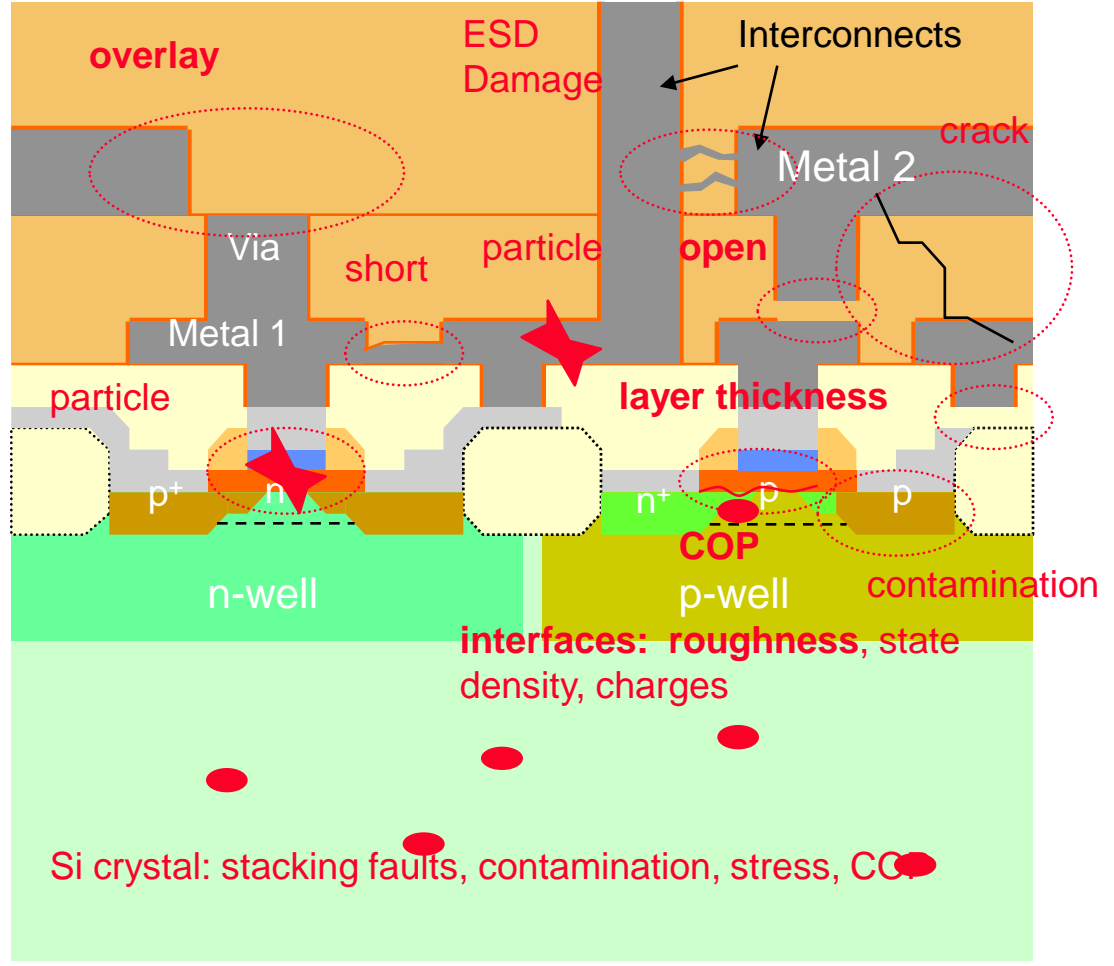
- a series of processes with up to 1000 processing steps
- a series of interposed metrology and inspection steps

Metrology for semiconductor manufacturing comprises tackling of preparatory know-how, of off-line, in-line and *in situ* – characterization, and advanced process control (APC).

Introduction

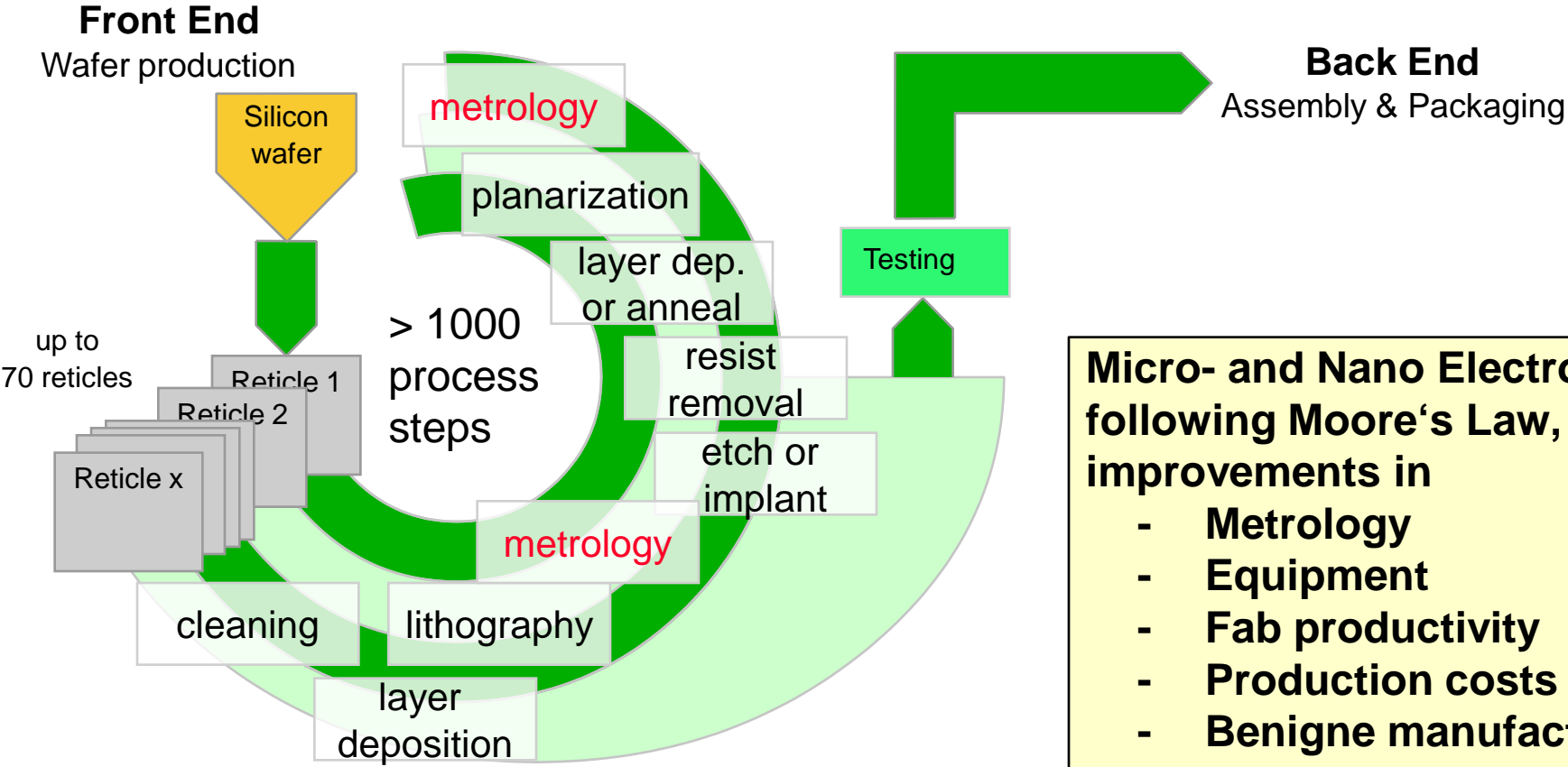


Defect and Failure Scenario of an Integrated Circuit



Metrology ins Semiconductor Manufacturing

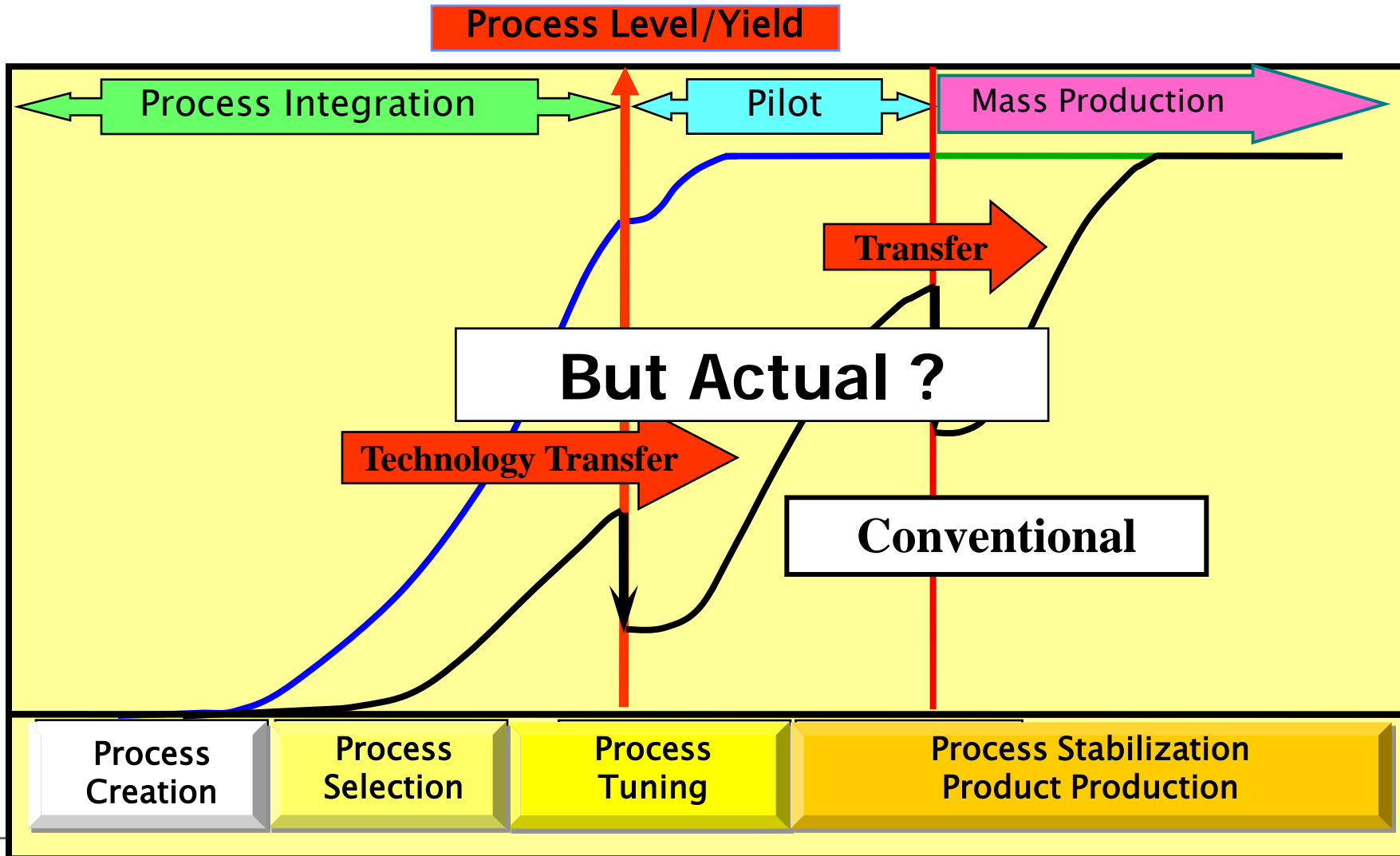
Metrology in Production



Micro- and Nano Electronics, following Moore's Law, require improvements in

- Metrology
- Equipment
- Fab productivity
- Production costs
- Benigne manufacturing

Actual Process and Yield Learning Curve



Metrology for Semiconductor Manufacturing: Tool Development

Typical Production Ramp Curve (Definition ITRS)

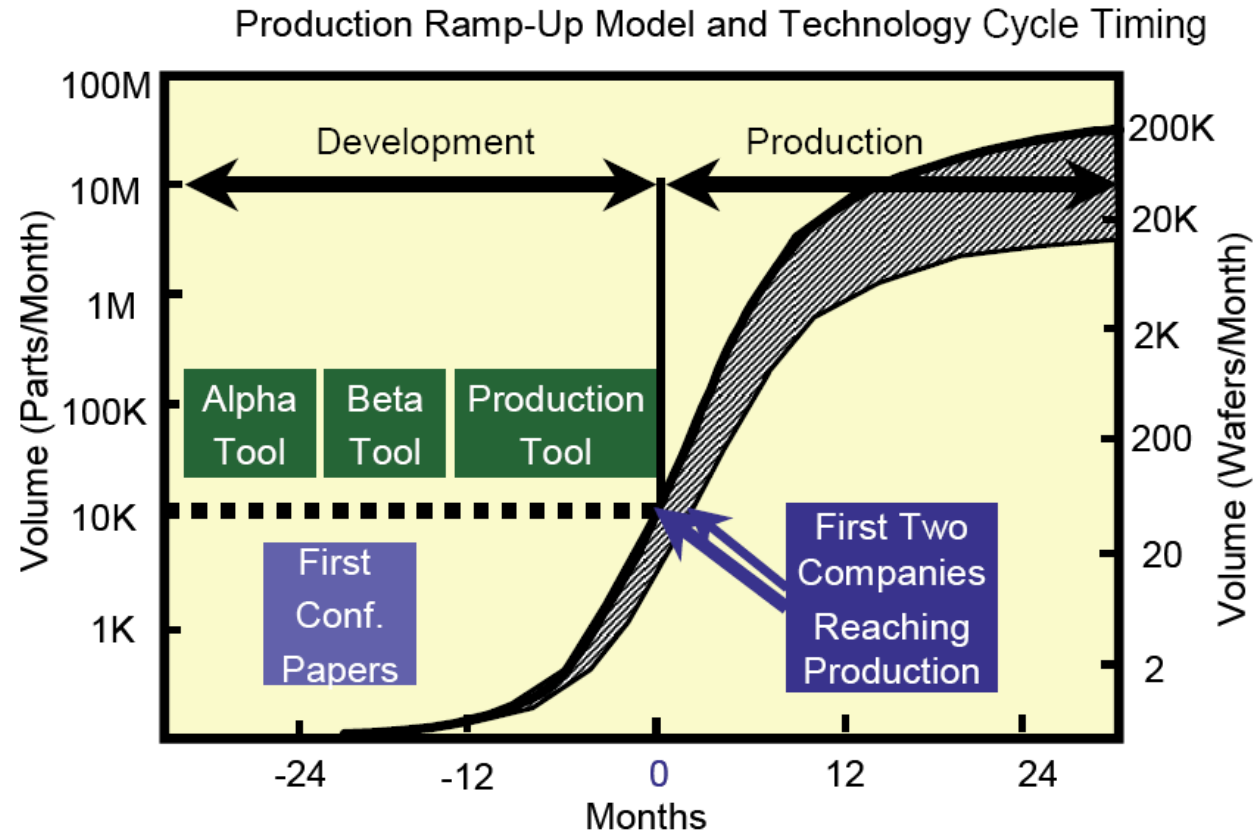


Figure 2 A Typical Production "Ramp" Curve



450 mm Metrology Tools

Impact of 450 mm Wafer Diameter on Equipment and Metrology

Diameter	300 mm	450 mm
Thickness	775 μm	775 μm
Area	706 cm^2	1589 cm^2

Impacted Areas	Focus Items
Processes	uniformity of processes, contamination, thermal effects/uniformity, (cleaning, polishing, deposition, etch, anneal, ..)
Lithography	increase of area by 2.25 times requires high performance – high speed litho
Handling	deformation (\rightarrow stress), transport issues, wafer translation (large distances, acceleration and settling times increase, vertical drift along the wafer)
Metrology	stages and handling, mapping capabilities, increase of area by 2.25 times requires high performance – high speed metrology (inspection), dimensional change due to thermal expansion coefficient, ...
Data Management	amount of data, data quality, ...



450 mm Metrology Tools

Potential Development Topics for 450mm Metrology Tools:

Stand-alone metrology

- Improved scatterometry (3D)
- Particle measurement
- Contamination monitoring
- Stress measurement on nanoscale
- Metrology tools for characterization of dielectrics, ultra-thin layers and interfaces (composition, morphology, geometric dimensions)
- Reference materials

Data processing and algorithms

- Algorithms for the measurements of complex stacks and features
- Models for the analysis of ultra-thin layers including interface and quantum effects
- Data reduction algorithms for correlated sampling approach and calculation of quality data
- Model for quantification of precision trade-off of IM to stand-alone metrology vs. improved sampling rate and time based information

Integrated metrology and sensors

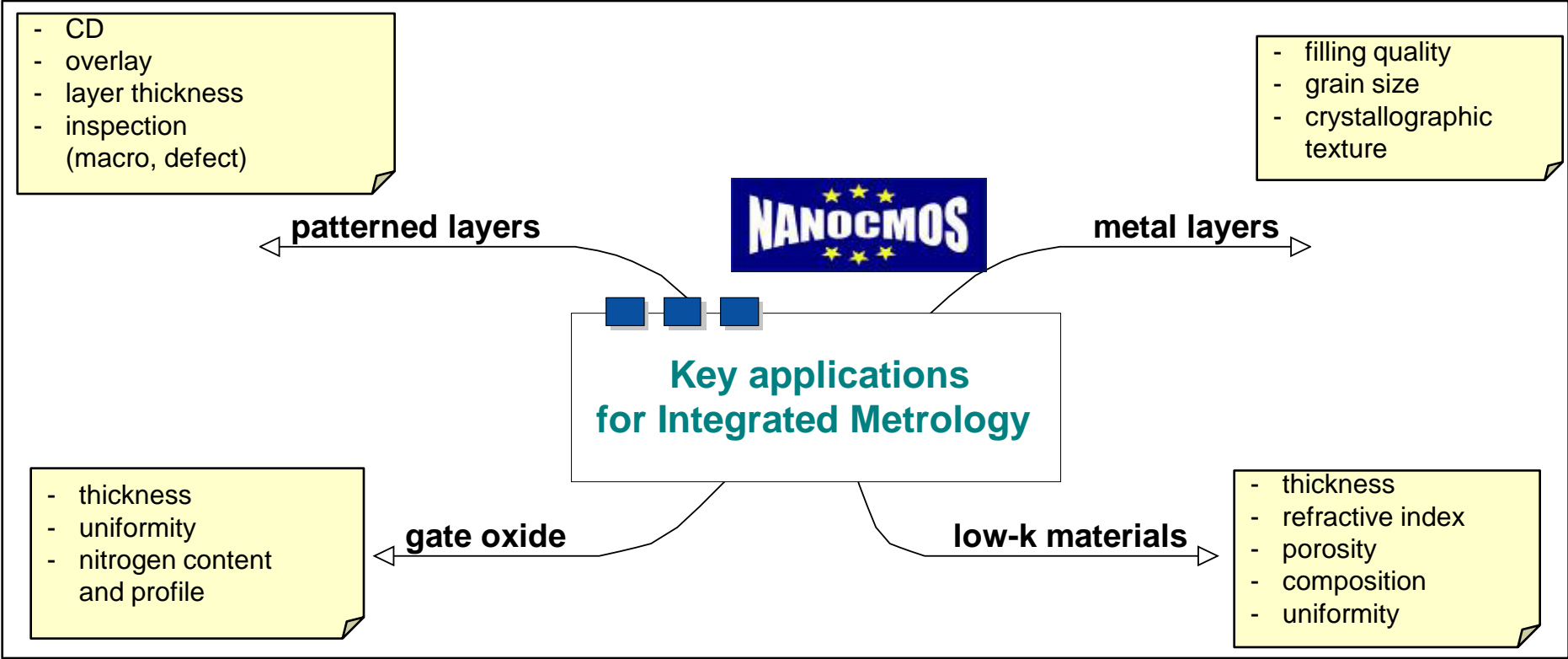
- Sensors for improved equipment characterization and qualification
- Sensors for characterization of plasma, litho, and CMP processes



450 mm Metrology Tools

Priorities in 450 mm

- to be defined by end-users (target specs, required improvements/modifications)
- may not differ from current ones, e.g. NANOCMOS



Contributions by IISB

450mm Platforms for Metrology Development → Fraunhofer supported by LETI and IMEC ready to provide

- **Stand-alone metrology:** Realization of a 450 mm metrology platform, which enables the development of individual core metrology systems for 450 mm metrology requirements without the need to supply overhead wafer handling equipment, open automation, and fab data management.
- **Integrated metrology and sensors:** Realization of test beds to realize common standardized integration and automation strategies for the development of IM and sensors without the need to supply overhead automation, and fab data management.

R&D Activities for 450 mm Metrology → Fraunhofer ready to start

- IISB metrology and expertise applicable to 450 mm: wave front sensors, scatterometry, ellipsometry, digital imaging and processing, defect inspection, x-ray techniques
- equipment qualification/development: organic/inorganic contamination, thermo desorption, TXRF, vapor phase composition
- advanced sensor development for Stand-alone and integrated metrology
- virtual metrology and innovative APC concepts



Support Activities for 450 mm Metrology Equipment Development

- preparation of test wafers and reference samples, e.g. with controlled deposition of contaminants and defects
- cleaning and polishing (double and single side)
- definition of standardized wafer for 450 mm wafer exchange amongst R&D sites using accepted specifications
- development of standards
- Set-up of distributed processing network including logistics for 450 mm

Summary & Outlook

- Metrology is the onset of the food chain
- Currently, appropriate modification of existing metrology tools is sufficient for starting 450 mm development
- support of equipment suppliers in the transition to 450 mm and towards novel metrology challenges
- 4 D metrology
- IISB will provide 450 mm atmospheric stage and 450 mm vacuum stage with (standardized?) sensor and metrology components accommodation
- Integration of metrology will be continued by IISB
- Global collaboration is mandatory in research and with industry
- Europe offers to share 450 mm development by a focus on 450 mm metrology



Thank you

